6	5	4	3 1	2 1	<u> </u>	
BRS	BRS	BRS	IS&R	IS&R	IS&R	Туре
L11	L10	L9	L8	L7	97	L#
82120	106203	5473	,	—	5	Hits
NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	CMOS or "CMOS"	differen\$4 with (oxygen or O2 or "O2" or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1	("6677652").PN.	("6750519").PN.	(("6043157") or ("6087231") or ("6083836") or ("5266519") or ("6475908")).PN.	Search Text
USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; US-PGPUB	USPAT; US-PGPUB	USPAT; US-PGPUB	DBs
2004/07/08 18:33	2004/07/08 18:33	2004/07/08 19:24	2004/07/08 18:30	2004/07/08 17:20	2004/07/08 17:06	Time Stamp
		,				Com ments
						Error Defini tion
0	0	0	0	0	0	Er ro

0			2004/07/08 18:47	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	conduct\$5 adj oxide\$1	7241	L17	BRS	12
0			2004/07/08 18:36	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	9 and 13 and 14 and 15	10	L16	BRS	11
0			2004/07/08 18:35	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	work\$3 near3 function\$1	33191	L15	BRS	10
0			2004/07/08 18:58	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	metal adj5 gate\$1	21484	L14	BRS	9
0			2004/07/08 18:34	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	10 or (11 and 12)	133038	L13	BRS	∞
0			2004/07/08 18:34	USPAT; US-PGPUB; -EPO; JPO; DERWENT; IBM_TDB	USPAT; UPMOS\$4 or P-MOS\$4 or EPO; JPO; DERWEN' IBM_TDB	66079	L12	BRS	7
Er ro	Error Er Definiro tion rs	Com ments	Time Stamp	DBs	Search Text	Hits	L#	Type	

0			2004/07/08 18:55	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	22 and 9	6	L23	BRS	18
0			2004/07/08 18:55	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	USPAT; U 13 and (14 or 17 or 18 or EPO; JPO; 20) and 15 and 21 IBM_TDB	59	L22	BRS	17
0			2004/07/08 19:14	·USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	(implant\$8 or inject\$4 or USPAT; US-PGPUB; dop\$5) near15 (oxygen EPO; JPO; or O2 or "O2" or DERWENT; "O.sub.2") [BM_TDB]	35882	L21	BRS	16
0			2004/07/08 18:50	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	conduct\$5 adj oxide adj gate\$1	2	L20	BRS	15
0			2004/07/08 18:48	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re	164401 4	L19	BRS	14
0			2004/07/08 18:47	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	metal adj oxide adj gate\$1	139	L18	BRS	13
Er ro	Error Er Definiro tion rs	Com ments	Time Stamp	DBs	Search Text	Hits	L#	Туре	

0			2004/07/08	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	(differen\$4 or var\$6 or dissimilar\$4 or divers\$6) USPAT; US-PGPUB; with (oxygen or O2 or "O2" or "O.sub.2" or DERWENT; oxide or oxides) with IBM_TDB concentration\$1	10792	L28	BRS	23
0			2004/07/08 19:19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	26 and 15	32	L27	BRS	22
0			2004/07/08 19:18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	(24 or 20 or 18 or 17) and 25	314	L26 314	BRS	21
0			2004/07/08 19:17	PGPUB;	(implant\$8 or inject\$4 or USPAT; US-PGPUB; dop\$5) with (oxygen or EPO; JPO; O2 or "O2" or "O.sub.2") DERWENT; with (19 or metal\$2) IBM_TDB	3756	1.25	BRS	20
0			2004/07/08 18:59	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	(metal or 19) near15 gate\$1	61576	124	BRS	19
r Er ii ro rs	Error Er Definiro tion rs	Com ments	Time Stamp	DBs	Search Text	Hits	L#	Туре	

	Type L#	L#	Hits	Search Text	DBs	Time Stamp	Com liments	Com Definiro ments tion rs	rs er
24 I	24 BRS L29 45	L29		USPAT; U 28 and (24 or 20 or 18 or EPO; JPO; 17 or 14) and 15 IBM TDB	S-PGPUB; Г;	2004/07/08 19:29			

L Number	Hits	Search Text	DB	Time stamp
6	5	(("6043157") or ("6087231") or ("6083836") or ("5266519") or	USPAT;	2004/07/08 17:06
		("6475908")).PN.	US-PGPUB	
7	1	("6750519").PN.	USPAT;	2004/07/08 17:20
			US-PGPUB	
8	1	("6677652").PN.	USPAT;	2004/07/08 18:30
			US-PGPUB	
9	5473	differen\$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides)	USPAT;	2004/07/08 19:24
		with concentration\$1	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	10/202	G) (O) G) (O)	IBM_TDB	2004/07/09 18:22
10	106203	CMOS or "CMOS"	USPAT;	2004/07/08 18:33
i i			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
11	92120	NIMOSEA NIMOSEA (NI adia MOSEA)	IBM_TDB	2004/07/09 19:22
11	82120	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT; US-PGPUB;	2004/07/08 18:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
12	66079	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT;	2004/07/08 18:34
12	00079	1 1 1/10544 of 1 -1/10544 of (1 adj5 1/10544)	US-PGPUB;	2004/07/00 10:54
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
13	133038	(CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4))	USPAT;	2004/07/08 18:34
	155050	and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))	US-PGPUB;	
			EPO, JPO,	
			DERWENT;	
			IBM_TDB	
14	21484	metal adj5 gate\$1	USPAT;	2004/07/08 18:58
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	2004/05/00 10 25
15	33191	work\$3 near3 function\$1	USPAT;	2004/07/08 18:35
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
16	10	(differen\$4 with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides)	USPAT;	2004/07/08 18:36
16	10	with concentration\$1) and ((CMOS or "CMOS") or ((NMOS\$4 or	US-PGPUB;	2004/07/08 18:50
		N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3	ЕРО; ЛРО;	
		MOS\$4)))) and (metal adj5 gate\$1) and (work\$3 near3 function\$1)	DERWENT;	
			IBM_TDB	
17	7241	conduct\$5 adj oxide\$1	USPAT;	2004/07/08 18:47
			US-PGPUB;	
			ЕРО, ЈРО,	
			DERWENT;	
			IBM_TDB	
18	139	metal adj oxide adj gate\$1	USPAT;	2004/07/08 18:47
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/07/00 10 10
19	1644014	ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or	USPAT;	2004/07/08 18:48
		Rhenium or Re	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	I		IBM_TDB	l

20		1.405 1''1. 1'4-01	TIOD AT:	2004/07/08 18.50
20	2	conduct\$5 adj oxide adj gate\$1	USPAT; US-PGPUB;	2004/07/08 18:50
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
21	35882	(implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or	USPAT;	2004/07/08 19:14
		"O.sub.2")	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
22	59	((CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4))	USPĀT;	2004/07/08 18:55
		and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and ((metal adj5	US-PGPUB;	
		gate\$1) or (conduct\$5 adj oxide\$1) or (metal adj oxide adj gate\$1) or	ЕРО; ЛРО;	
		(conduct\$5 adj oxide adj gate\$1)) and (work\$3 near3 function\$1) and ((implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or	DERWENT; IBM_TDB	
		"O.sub.2"))	IDIVI_IDD	
23	6	(((CMOS or "CMOS") or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4))	USPAT;	2004/07/08 18:55
		and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and ((metal adj5	US-PGPUB,	
		gate\$1) or (conduct\$5 adj oxide\$1) or (metal adj oxide adj gate\$1) or	ЕРО; ЛРО;	
		(conduct\$5 adj oxide adj gate\$1)) and (work\$3 near3 function\$1) and	DERWENT;	
		((implant\$8 or inject\$4 or dop\$5) near15 (oxygen or O2 or "O2" or "O.sub.2"))) and (differen\$4 with (oxygen or O2 or "O2" or "O.sub.2" or	IBM_TDB	
		oxide or oxides) with concentration\$1)		
24	61576	(metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or	USPAT;	2004/07/08 18:59
		Rhodium or Rh or Rhenium or Re)) near15 gate\$1	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT; IBM_TDB	
25	3756	(implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or "O2" or	USPAT;	2004/07/08 19:17
	3750	"O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium or Os or	US-PGPUB;	
		Rhodium or Rh or Rhenium or Re) or metal\$2)	ЕРО; ЈРО;	
:			DERWENT;	
26	214	(((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or	IBM_TDB USPAT;	2004/07/08 19:18
26	314	Rhodium or Rh or Rhenium or Re)) near15 gate\$1) or (conduct\$5 adj	US-PGPUB;	2004/07/08 17:18
		oxide adj gate\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj	ЕРО; ЛРО;	
		oxide\$1)) and ((implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or	DERWENT;	
		"O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium	IBM_TDB	
	20	or Os or Rhodium or Rh or Rhenium or Re) or metal\$2))	LICDAT.	2004/07/08 19:19
27	32	((((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)) near 15 gate \$1) or (conduct \$5 adj	USPAT; US-PGPUB;	2004/07/08 19.19
		oxide adj gate\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj	ЕРО; ЛРО;	
		oxide\$1)) and ((implant\$8 or inject\$4 or dop\$5) with (oxygen or O2 or	DERWENT;	
		"O2" or "O.sub.2") with ((ruthenium or Ru or Iridium or Ir or Osmium	IBM_TDB	
		or Os or Rhodium or Rh or Rhenium or Re) or metal\$2))) and (work\$3		
28	10792	near3 function\$1) (differen\$4 or var\$6 or dissimilar\$4 or divers\$6) with (oxygen or O2 or	USPAT;	2004/07/08 19:27
20	10772	"O2" or "O.sub.2" or oxide or oxides) with concentration\$1	US-PGPUB;	
		'	ЕРО; ЛРО;	
			DERWENT;	
20	1.5	(/3:00	IBM_TDB	2004/07/09 10:20
29	45	((differen\$4 or var\$6 or dissimilar\$4 or divers\$6) with (oxygen or O2 or "O2" or "O.sub.2" or oxide or oxides) with concentration\$1) and	USPAT; US-PGPUB;	2004/07/08 19:29
		(((metal or (ruthenium or Ru or Iridium or Ir or Osmium or Os or	EPO; JPO;	
		Rhodium or Rh or Rhenium or Re)) near 15 gate \$1) or (conduct \$5 adj	DERWENT;	
		oxide adj gate\$1) or (metal adj oxide adj gate\$1) or (conduct\$5 adj	IBM_TDB	
	0.4205	oxide\$1) or (metal adj5 gate\$1)) and (work\$3 near3 function\$1)	I I CD A TO	2004/07/09 19:22
-	94396	CMOS	USPAT; US-PGPUB;	2004/07/08 18:32
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	

	72476	ND (OCC) - NI MOCCA OI - 1:2 MOCCA)	TIODAT:	2004/07/09 10:22
-	73476	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT; US-PGPUB;	2004/07/08 18:33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	58888	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT;	2004/07/08 18:33
-	20000	riviosa4 of r-iviosa4 of (r aujs iviosa4)		2004/07/08 18.55
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	19024		IBM_TDB	2004/07/08 18:34
-	18924	metal adj5 gate\$1	USPAT; US-PGPUB;	2004/07/06 16.34
	1		EPO; JPO;	
			DERWENT;	
			IBM TDB	
	29246	work\$3 near3 function\$1	USPAT;	2004/07/08 18:35
-	29240	work\$3 near3 lunction\$1		2004/0//08 18.33
ŀ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	118169	CMOS or (AIMOSSA or NI MOSSA or Al adia Mossa) and (DMOSSA)	IBM_TDB USPAT;	2003/09/30 16:53
-	118109	CMOS or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4		2003/09/30 10.33
		or P-MOS\$4 or (P adj3 MOS\$4)))	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	422	(matched 5 gate(1) and (world 2 mag 5 function(1) and (CMOS or	USPAT;	2003/09/27 15:30
-	432	(metal adj5 gate\$1) and (work\$3 near3 function\$1) and (CMOS or	US-PGPUB;	2003/03/27 13.30
		((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or	EPO; JPO;	
		P-MOS\$4 or (P adj3 MOS\$4))))	DERWENT;	
			IBM_TDB	
	05027	CMOS or "CMOS" or (complementary adj metal adj oxide adj	USPAT;	2003/09/30 16:53
-	95937	(semiconduct\$4 or silicon))	US-PGPUB;	2003/07/30 10.55
		(Semiconductor of Sincon))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	73591	NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)	USPAT;	2003/09/30 16:54
-	/5591	NIVIOSOFT OF NIVIOSOFT OF (IX days NIVIOSOFT)	US-PGPUB;	2005/05/50 10.5
			ЕРО; ЛРО;	
	1		DERWENT;	
	1		IBM_TDB	
l <u> </u>	58981	PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)	USPAT;	2003/09/30 16:54
		The state of the s	US-PGPUB;	
			ЕРО; ЛРО;	
		·	DERWENT;	
			IBM_TDB	
_	119584	(CMOS or "CMOS" or (complementary adj metal adj oxide adj	USPAT;	2003/09/30 16:55
		(semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3	US-PGPUB;	
		MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))	ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	
-	31830	work\$3 near3 function\$3	USPĀT;	2003/09/30 16:56
1			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	6415	conduct\$5 adj oxide\$1	USPAT;	2004/07/08 18:47
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT,	
1			IBM_TDB	

			7700	0004/07/00
-	106	metal adj oxide adj gate\$1	USPAT;	2004/07/08 18:47
			US-PGPUB; EPO; JPO;	
	,		DERWENT;	
			IBM_TDB	
-	8	((CMOS or "CMOS" or (complementary adj metal adj oxide adj	USPAT;	2003/09/30 16:57
i		(semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3	US-PGPUB;	
1	[MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and	ЕРО; ЛРО;	
1		(work\$3 near3 function\$3) and (metal adj oxide adj gate\$1)	DERWENT;	
			IBM_TDB	
-	14	6027961.URPN.	USPAT	2003/09/30 17:06
-	3	6365450.URPN.	USPAT	2003/09/30 17:39
-	4	("5966597" "6033963" "6087208" "6087231").PN.	USPAT	2003/09/30 17:41
-	1455017	("4605947" "5268590" "5457580" "5600169" "5923999").PN.	USPAT	2003/09/30 17:42
-	1455017	ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or	USPAT;	2004/07/08 18:48
		Rhenium or Re	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	16402	(ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or	USPAT;	2003/09/30 18:39
-	10402	Rhenium or Re) and ((CMOS or "CMOS" or (complementary adj metal	US-PGPUB;	2003/07/30 10.37
	•	adj oxide adj (semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4	EPO; JPO;	
	•	or (N adj3 MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))	DERWENT;	
	1	(-:	IBM TDB	
-	631	(work\$3 near3 function\$3) and ((ruthenium or Ru or Iridium or Ir or	USPAT;	2003/09/30 18:40
		Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or	US-PGPUB;	
		"CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or	ЕРО; ЛРО;	
		silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and	DERWENT;	
		(PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))))	IBM_TDB	
-	102	(ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or	USPAT;	2003/09/30 18:41
		Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with	US-PGPUB;	
		(gate\$1 or electrode\$1)	ЕРО; ЈРО;	
1			DERWENT;	
	_	(/ 1.02 - 2.6-4) - 02 - 1 (/-4hi	IBM_TDB	2003/09/30 18:41
-	5	((work\$3 near3 function\$3) and ((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re) and ((CMOS or	USPAT; US-PGPUB;	2003/09/30 18.41
		"CMOS" or (complementary adj metal adj oxide adj (semiconduct\$4 or	ЕРО; ЛРО;	
		silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and	DERWENT;	
		(PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4))))) and ((ruthenium or Ru	IBM_TDB	
		or Iridium or Ir or Osmium or Os or Rhodium or Rh or Rhenium or Re)	_	
		with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with (gate\$1 or		
		electrode\$1))		
-	4742	metal adj gate\$1	USPAT;	2003/09/30 18:47
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT;	
			IBM_TDB	2002/00/20 10 12
-	29	(metal adj oxide adj gate\$1) and (metal adj gate\$1)	USPAT;	2003/09/30 18:47
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
	2	conduct\$5 adj oxide adj gate\$1	USPAT;	2004/07/08 18:48
-		Conducted and Oxide and Batchi	US-PGPUB;	2007/07/00 10:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	(((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh	USPAT;	2003/09/30 19:24
		or Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4))	US-PGPUB;	
		with (gate\$1 or electrode\$1)) and ((CMOS or "CMOS" or	ЕРО; ЛРО;	
		(complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or	DERWENT;	
		((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or	IBM_TDB	
	<u> </u>	P-MOS\$4 or (P adj3 MOS\$4))))) and (work\$3 near3 function\$3)		<u> </u>

	89	(/mithonium on Du on Indium on Ir on Comium on Oc on Dhodium on Dh	USPAT;	2003/09/30 19:24
-	89	((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh	US-PGPUB;	2003/09/30 19.24
		or Rhenium or Re) with (NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) with (gate\$1 or electrode\$1)) and ((CMOS or "CMOS" or	EPO; JPO;	
		(complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or	DERWENT;	
		((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or	IBM_TDB	
		P-MOS\$4 of (P adj3 MOS\$4))))	IDM_IDD	
	6778	(ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh or	USPAT;	2003/09/30 19:33
-	0//8	1 '	US-PGPUB:	2003/03/30 13.33
		Rhenium or Re) near15 gate\$1	EPO: JPO:	
			DERWENT;	
			IBM TDB	
	1225	((CMOS or "CMOS" or (complementary adj metal adj oxide adj	USPAT;	2003/09/30 19:34
-	1223	(semiconduct\$4 or silicon))) or ((NMOS\$4 or N-MOS\$4 or (N adj3	US-PGPUB;	2005/05/50 15.54
		MOS\$4)) and (PMOS\$4 or P-MOS\$4 or (P adj3 MOS\$4)))) and	EPO; JPO;	
		((ruthenium or Ru or Iridium or Ir or Osmium or Os or Rhodium or Rh	DERWENT;	
ļ		or Rhenium or Re) near15 gate\$1)	IBM TDB	
١.	75	(work\$3 near3 function\$3) and (((CMOS or "CMOS" or	USPAT;	2003/09/30 19:34
		(complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or	US-PGPUB;	
		((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or	ЕРО; ЛРО;	
		P-MOS\$4 or (P adj3 MOS\$4)))) and ((ruthenium or Ru or Iridium or Ir	DERWENT;	
		or Osmium or Os or Rhodium or Rh or Rhenium or Re) near15 gate\$1))	IBM TDB	
-	44	(metal adj oxide adj gate\$1) and ((CMOS or "CMOS" or	USPĀT;	2003/09/30 20:01
		(complementary adj metal adj oxide adj (semiconduct\$4 or silicon))) or	US-PGPUB,	
		((NMOS\$4 or N-MOS\$4 or (N adj3 MOS\$4)) and (PMOS\$4 or	ЕРО; ЛРО;	
	1	P-MOS\$4 or (P adj3 MOS\$4))))	DERWENT;	,
			IBM_TDB	